

Ds
gas formulation being free of SF₆, and a ratio of flow rates of CHF₃:argon:chlorine in the formulation is 5 to 80 sccm:5 to 80 sccm:5 to 60 sccm.

D3
21. (Amended) An oxygen-free plasma etching gas formulation for removing an organic ARC on a metallic layer comprising more than one fluorine-containing compound, an optional inert carrier gas, and chlorine, the gas formulation being free of SF₆.